



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



NE5550279A

Data Sheet
R09DS0033EJ0200
Rev.2.00
Jul 04, 2012

Silicon Power LDMOS FET

FEATURES

- High Output Power : $P_{out} = 33.0$ dBm TYP. ($V_{DS} = 7.5$ V, $I_{Dset} = 40$ mA, $f = 460$ MHz, $P_{in} = 15$ dBm)
- High power added efficiency : $\eta_{add} = 68\%$ TYP. ($V_{DS} = 7.5$ V, $I_{Dset} = 40$ mA, $f = 460$ MHz, $P_{in} = 15$ dBm)
- High Linear gain : $G_L = 22.5$ dB TYP. ($V_{DS} = 7.5$ V, $I_{Dset} = 40$ mA, $f = 460$ MHz, $P_{in} = 0$ dBm)
- High ESD tolerance
- Suitable for VHF to UHF-BAND Class-AB power amplifier.

APPLICATIONS

- 150 MHz Band Radio System
- 460 MHz Band Radio System
- 900 MHz Band Radio System

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
NE5550279A	NE5550279A-A	79A (Pb Free)	W7	<ul style="list-style-type: none"> • 12 mm wide embossed taping • Gate pin faces the perforation side of the tape
NE5550279A-T1	NE5550279A-T1-A			<ul style="list-style-type: none"> • 12 mm wide embossed taping • Gate pin faces the perforation side of the tape • Qty 1 kpcs/reel
NE5550279A-T1A	NE5550279A-T1A-A			<ul style="list-style-type: none"> • 12 mm wide embossed taping • Gate pin faces the perforation side of the tape • Qty 5 kpcs/reel

Remark To order evaluation samples, please contact your nearby sales office.

Part number for sample order: NE5550279A-A

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V_{DS}	30	V
Gate to Source Voltage	V_{GS}	6.0	V
Drain Current	I_{DS}	0.6	A
Drain Current (50% Duty Pulsed)	$I_{DS-pulse}$	1.2	A
Total Power Dissipation ^{Note}	P_{tot}	6.25	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note: Value at $T_C = 25^\circ\text{C}$

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

NE5550279A

RECOMMENDED OPERATING RANGE ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}		–	7.5	9.0	V
Gate to Source Voltage	V_{GS}		1.65	2.20	2.85	V
Drain Current	I_{DS}		–	0.4	–	A
Input Power	P_{in}	$f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V}$	–	15	20	dBm

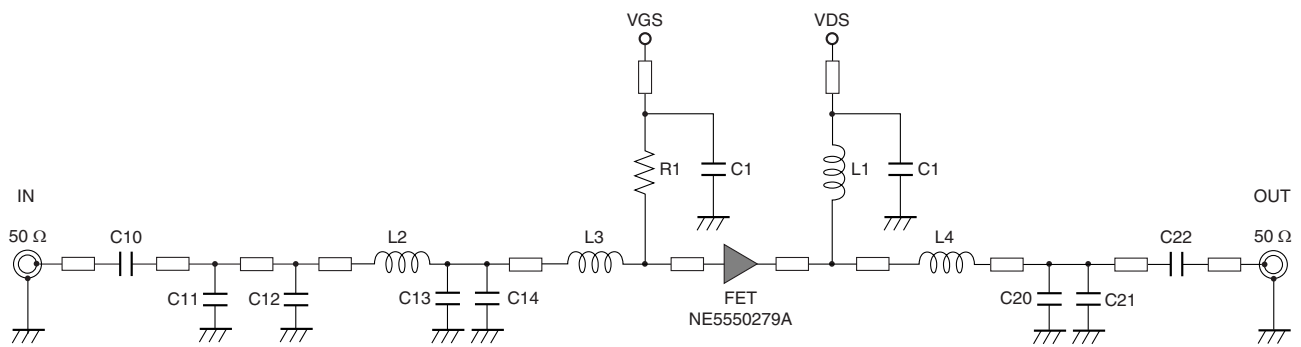
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = 6.0 \text{ V}$	–	–	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I_{DSS}	$V_{DS} = 25 \text{ V}$	–	–	10	μA
Gate Threshold Voltage	V_{th}	$V_{DS} = 7.5 \text{ V}, I_{DS} = 1.0 \text{ mA}$	1.15	1.65	2.25	V
Drain to Source Breakdown Voltage	BV_{DSS}	$I_{DS} = 10 \mu\text{A}$	25	38	–	V
Transconductance	G_m	$V_{DS} = 7.5 \text{ V}, I_{DS} = 140 \pm 20 \text{ mA}$	0.36	0.44	0.58	S
Thermal Resistance	R_{th}	Channel to Case	–	20.0	–	$^\circ\text{C/W}$
RF Characteristics						
Output Power	P_{out}	$f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V},$	31.5	33.0	–	dBm
Drain Current	I_{DS}	$P_{in} = 15 \text{ dBm},$	–	0.38	–	A
Power Drain Efficiency	η_d	$I_{Dset} = 40 \text{ mA (RF OFF)}$	–	70	–	%
Power Added Efficiency	η_{add}		–	68	–	%
Linear Gain	G_L ^{Note}		–	22.5	–	dB

Note: $P_{in} = 0 \text{ dBm}$

Remark DC performance is 100% testing. RF performance is testing several samples per wafer.
Wafer rejection criteria for standard devices is 1 reject for several samples.

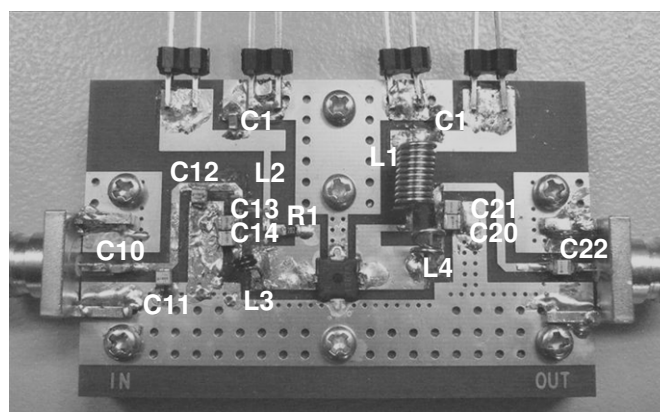
TEST CIRCUIT SCHEMATIC FOR 460 MHz



COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

Symbol	Value	Type	Maker
C1	1 μ F	GRM188B31C105KA92	Murata
C10	22 pF	GRM1882C1H220JA01	Murata
C11	1.2 pF	ATC100A1R2JW	American Technical Ceramics
C12	4.7 pF	ATC100A4R7BW	American Technical Ceramics
C13	15 pF	ATC100A150BW	American Technical Ceramics
C14	12 pF	ATC100A120BW	American Technical Ceramics
C20	10 pF	ATC100A100JW	American Technical Ceramics
C21	3.9 pF	ATC100A3R9BW	American Technical Ceramics
C22	100 pF	ATC100A101JW	American Technical Ceramics
R1	2 k Ω	1/10 W Chip Resistor RK73B1JTDD202J	KOA
L1	123 nH	ϕ 0.5 mm, ϕ D = 3 mm, 10 Turns	Ohesangyou
L2	10 nH	LQW18AN10NG00	Murata
L3	9.8 nH	ϕ 0.4 mm, ϕ D = 1.6 mm, 3 Turns	Ohesangyou
L4	20 nH	ϕ 0.5 mm, ϕ D = 3 mm, 2 Turns	Ohesangyou
PCB	–	R4775, t = 0.4 mm, ϵ r = 4.5, size = 30 \times 48 mm	Panasonic
SMA Connector	–	WAKA 01K0790-20	WAKA

COMPONENT LAYOUT OF TEST CIRCUIT FOR 460 MHz

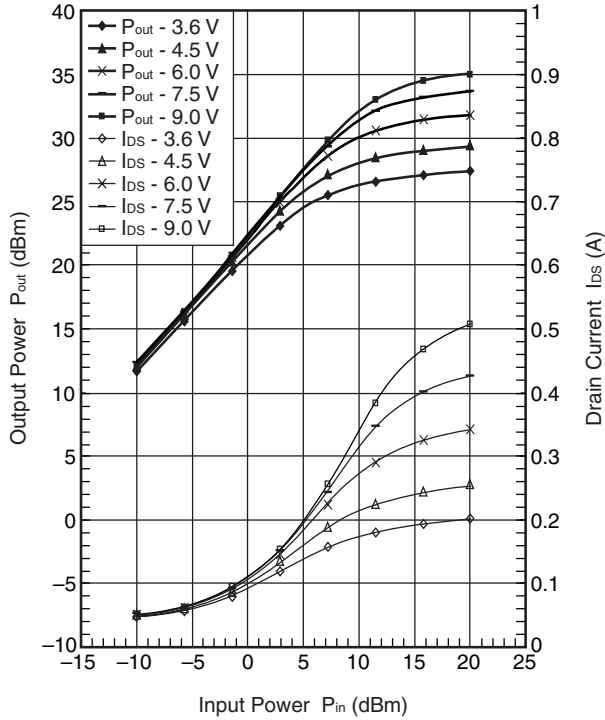


TYPICAL CHARACTERISTICS 1 (T_A = 25°C)

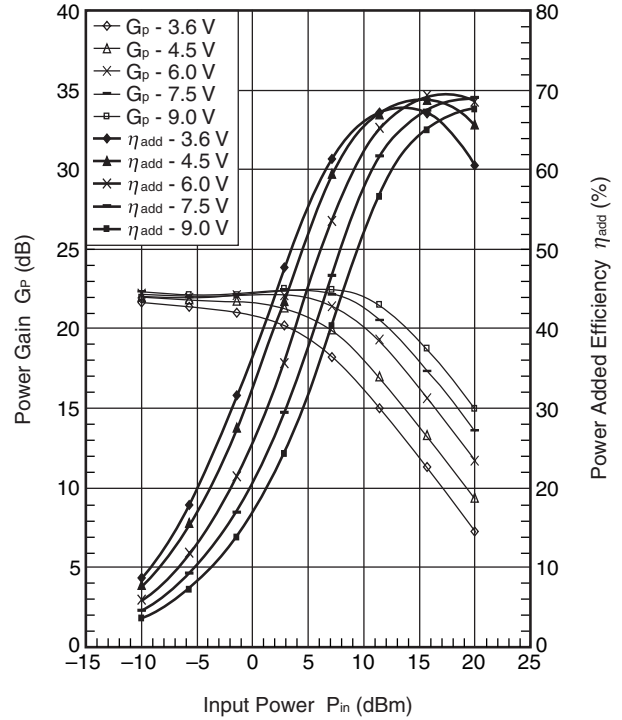
R: f = 460 MHz, V_{DS} = 3.6/4.5/6/7.5/9 V, I_{Dset} = 40 mA, P_{in} = -10 to 20 dBm

IM: f1 = 460 MHz, f2 = 461 MHz, V_{DS} = 3.6/4.5/6/7.5/9 V, I_{Dset} = 40 mA, P_{out} (2 tone) = 8 to 32 dBm

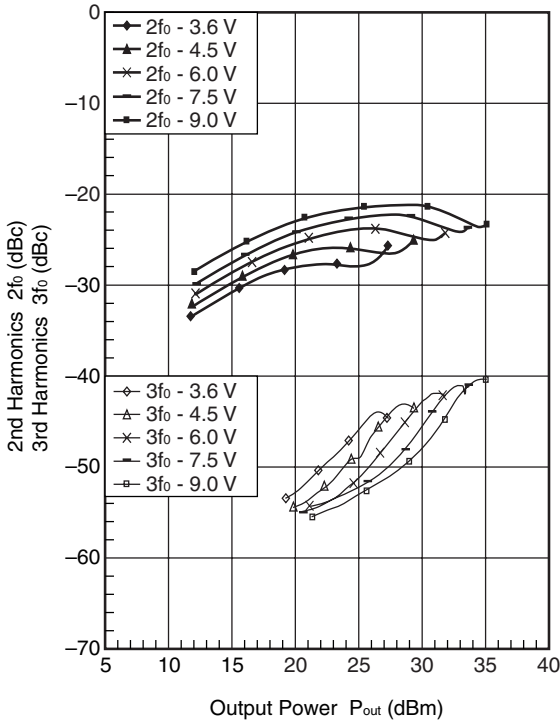
OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER



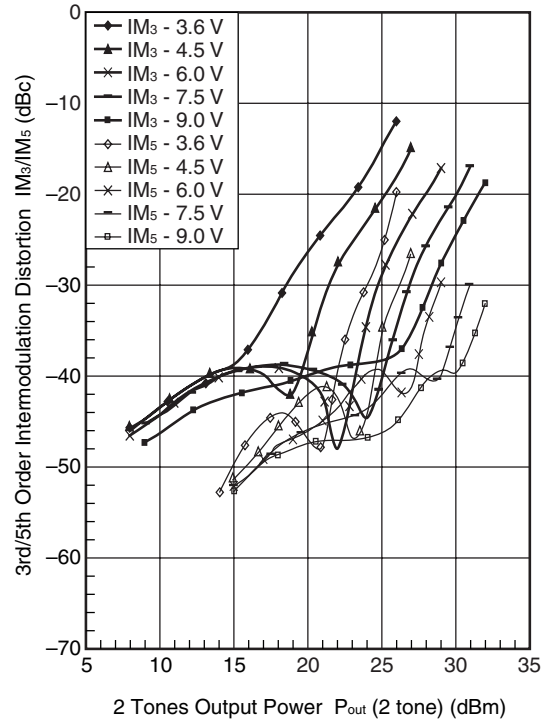
POWER GAIN, POWER ADDED EFFICIENCY vs. INPUT POWER



2f₀, 3f₀ vs. OUTPUT POWER



IM₃/IM₅ vs. 2 TONES OUTPUT POWER



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

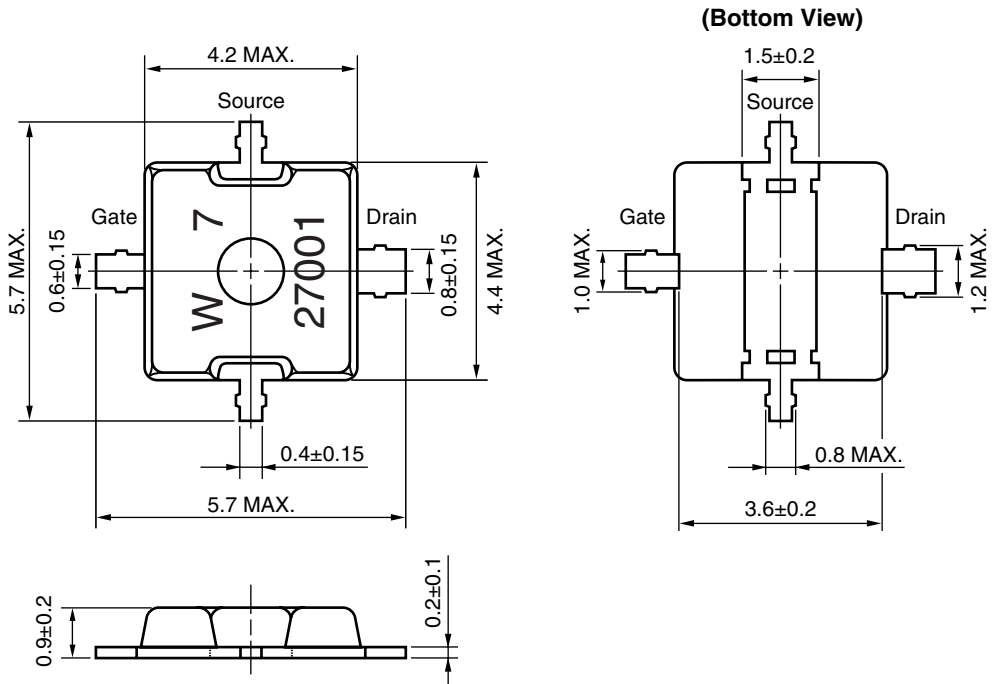
Click here to download S-parameters.

[Products] → [RF Devices] → [Device Parameters]

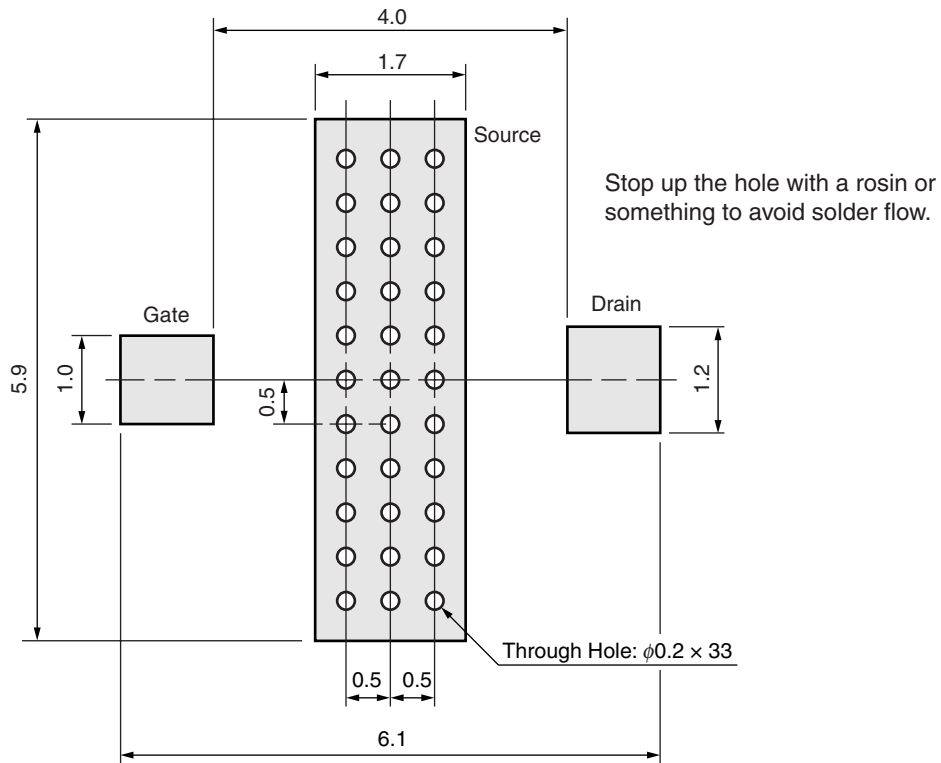
URL <http://www.renesas.com/products/microwave/>

PACKAGE DIMENSIONS

79A (UNIT: mm)



79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)



Revision History	NE5550279A Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Mar 28, 2012	-	First edition issued
2.00	Jul 04, 2012	p.2	Modification of ELECTRICAL CHARACTERISTICS

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